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Substitute for form 1449A/B/PTO		<b>Complete if Known</b>			
<b>INFORMATION DISCLOSURE STATEMENT BY APPLICANT</b>  (Use as many sheets as necessary)		Application Number	09/940,792-Conf.#5268		
		Filing Date	August 29, 2001		
		First Named Inventor	Paul A. Farrar et al.		
		Art Unit	2815		
		Examiner Name	E.C.H. Lee		
Sheet	1	of	11	Attorney Docket Number	M4065.0382/P382-A

U.S. PATENT DOCUMENTS						
Examiner Initials*	Cite No. <sup>1</sup>	Document Number		Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
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Examiner Signature					Date Considered	6/13/00

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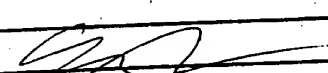
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Examiner Initials*	Cite No. <sup>1</sup>	Foreign Patent Document		Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear <sup>7</sup>	
		Country Code <sup>2</sup> -Number <sup>3</sup> -Kind Code <sup>4</sup> (if known)					
BA	EP 1030196			08/2000			
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\*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant. <sup>1</sup> Applicant's unique citation designation number (optional). <sup>2</sup> See Kinds Codes of USPTO Patent Documents at [www.uspto.gov](http://www.uspto.gov) or MPEP 901.04. <sup>3</sup> Enter Office that issued the document, by the two-letter code (WIPO Standard ST.3). <sup>4</sup> For Japanese patent documents, the indication of the year of the reign of the Emperor must precede the serial number of the patent document. <sup>5</sup> Kind of document by the appropriate symbols as indicated on the document under WIPO Standard ST.16 if possible. <sup>6</sup> Applicant is to place a check mark here if English language translation is attached.

Examiner Signature		Date Considered	8/13/06
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NON PATENT LITERATURE DOCUMENTS				
Examiner Initials	Cite No.	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T <sup>2</sup>	
EL	CA	ABE, T.; Nakano, M.; Itho, T.; Takei, T.; Uchiyama, A.; Yoshizawa, K.; Nakazato, Y., Silicon Wafer-Bonding Process Technology for SOI Structures, Extended Abstracts of the 22nd Int'l Conference on Solid State Devices and Materials, Sendai, (1990) 853-856.		
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EL	CC	ASOH, Hidetaka; Nishio, K.; Nakao, M.; Yokoo, A.; Tamaura, T.; Masuda, H., Fabrication of ideally ordered anodic porous alumina with 63 nm hole periodicity using sulfuric acid, J. Vac. Sci. Technol. B 19(2) Mar/April (2001) 569-572.		
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CT	BLANFORD, Christopher; Yan, H.; Schroden, R.C.; Al-Daous, M.; Stein, A., Gems of Chemistry and Physics: Macroporous Metal Oxides with 3D Order, Adv. Mater. 13(6) Mar 16, 2001, 401-407.	
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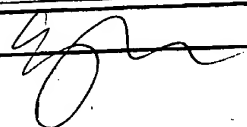
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		Art Unit	2815
		Examiner Name	E.C.H. Lee
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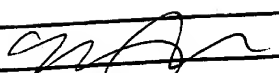
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				First Named Inventor	<b>Paul A. Farrar</b>
				Group Art Unit	<b>2612-2815</b>
				Examiner Name	<b>D. Zarnke Lee</b>
Sheet	<b>1</b>	of	<b>1</b>	Attorney Docket Number	<b>M4065.0382/P382-A</b>

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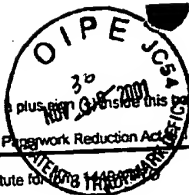
U.S. PATENT DOCUMENTS						
Examiner Initials*	Cite No. <sup>1</sup>	U.S. Patent Document		Name of Patentee or Applicant of Cited Document	Date of Publication of Cited Document MM-DD-YYYY	Pages, Columns, Lines, Where Relevant, Passages or Relevant Figures Appear
		Number	Kind Code <sup>2</sup> (if known)			
<i>W</i>	A	5,920,121		Forbes, et al.*	07/06/1999	
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<b>INFORMATION DISCLOSURE STATEMENT BY APPLICANT</b>  (use as many sheets as necessary)		<b>Complete if Known</b>	
		Application Number	09/940,792
		Filing Date	August 29, 2001
		First Named Inventor	Paul A. Farrar
		Group Art Unit	2812 2815
		Examiner Name	B. Zameke / lee
Attorney Docket Number	M4065.0382/P382-A		
Sheet	1	of	2

U.S. PATENT DOCUMENTS						
Examiner Initials*	Cite No. <sup>1</sup>	U.S. Patent Document		Name of Patentee or Applicant of Cited Document	Date of Publication of Cited Document MM-DD-YYYY	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
		Number	Kind Code <sup>2</sup> (if known)			
EL	A	5,963,838		Yamamoto et al.	10/15/1999	

FOREIGN PATENT DOCUMENTS								
Examiner Initials*	Cite No. <sup>1</sup>	Foreign Patent Document			Name of Patentee or Applicant of Cited Document	Date of Publication of Cited Document MM-DD-YYYY	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear	T <sup>3</sup>
		Office <sup>3</sup>	Number <sup>4</sup>	Kind Code <sup>5</sup> (if known)				

Examiner Signature		Date Considered	9/16/02
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\*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

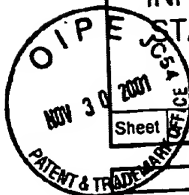
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<b>INFORMATION DISCLOSURE STATEMENT BY APPLICANT</b> (use as many sheets as necessary)		Application Number	09/940,792
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		Group Art Unit	2812 2815
		Examiner Name	D. Zameke Lee
Sheet 2 of 2	Attorney Docket Number	M4065.0382/P382-A	



OTHER PRIOR ART - NON PATENT LITERATURE DOCUMENTS		
Examiner Initials	Cite No. <sup>1</sup>	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc), date, page(s), volume-issue number(s), publisher, city and/or country where published.
CL	B	F.A. Nichols, et al. - "Surface- (Interface-) and Volume-Diffusion Contributions to Morphological Changes Driven by Capillarity," Transactions of the Metallurgical Society of AIME, Volume 233, October 1965, pgs. 1840-1848*
CL	C	Tsutomu Sato, et al. - "A New Substrate Engineering for the Formation of Empty Space in Silicon (ESS) Induced by Silicon Surface Migration," 1999 IEEE, pgs. 517-520*
CL	D	U.S. Application, Serial No. 09/069,346 filed April 29, 1998, Attorney docket #303.367US1, pgs. 1-22 w/6 shts. drwgs.*

Examiner Signature	Date Considered	9/16/02
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